

IGBT

High speed IGBT in Trench and Fieldstop technology
recommended in combination with SiC Diode IDH15S120

IGW25N120H3

1200V high speed switching series third generation

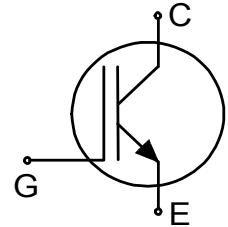
Data sheet

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Features:

TRENCHSTOP™ technology offering

- best in class switching performance: less than 500µJ total switching losses achievable
- very low V_{CEsat}
- low EMI
- maximum junction temperature 175°C
- qualified according to JEDEC for target applications
- Pb-free lead plating; RoHS compliant
- complete product spectrum and PSpice Models: <http://www.infineon.com/igbt/>



Applications:

- solar inverters
- uninterruptible power supplies
- welding converters
- converters with high switching frequency



Package pin definition:

- Pin 1 - gate
- Pin 2 & backside - collector
- Pin 3 - emitter



Key Performance and Package Parameters

Type	V_{CE}	I_C	$V_{CEsat}, T_{vj}=25^{\circ}C$	T_{vjmax}	Marking	Package
IGW25N120H3	1200V	25A	2.05V	175°C	G25H1203	PG-TO247-3